

Pending

Active

- L1: (1) 10/437060
- L2: (93) sidewall adj select adj gate
- L3: (279) sidewall adj floating adj gate
- L4: (20) 2 and 3
- L5: (131) trench adj floating adj gate
- L6: (3) dual adj profile adj trench
- L7: (38669) second adj opening
- L8: (56107) flash adj memory
- L9: (183) 7 and 8
- L10: (0) 5 and 9
- L11: (59) 9 and trench

Failed

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DBs: USPAT:US+GPUB:EPD:JPO:DERWENT:IBM:TOE
Default operator: OR

9 and trench

BRIS term: Gekom: Image: Text: HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cls	Inventor	S	C	P	A	3	Image 1
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040137696	20040715	22	Methods of forming semiconductor devices having field oxides in trenches	438/424			Kim, Hong-Soo et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040135184	20040715	58	Nonvolatile magnetic memory device and manufacturing method thereof	257/295			Motoyoshi, Makoto	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040113181	20040617	16	Lateral phase change memory and method thereof	257/246			Wicker, Guy C.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040051164	20040318	13	Two-transistor pixel with buried reset channel and method of formation	257/595			Fossum, Eric R.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040046195	20040311	54	Semiconductor integrated circuit device and process for manufacturing	257/296	257/198; 257/306;		Nakamura, Yoshitaka et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040043529	20040304	13	Two-transistor pixel with buried reset channel and method of formation	438/70			Fossum, Eric R.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040036124	20040226	18	Inverted staggered thin film transistor with salicidized source/drain structures	257/382	257/383; 257/384;		Vyvoda, Michael A. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030219951	20031127	18	Semiconductor constructions, and methods of forming semiconductor constructions	438/305	438/268		Gonzalez, Fernando	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030219943	20031127	9	METHOD OF FABRICATING A FLOATING GATE FOR SPLIT GATE	438/257	257/E21.209; 438/593		Lin, Chi-Hui et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030218208	20031127	19	Split gate flash memory cell and method for fabricating the same	257/316	257/318; 257/E21.692;		Lin, Chi-Hui et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20030216001	20031120	32	Non-volatile memory device having a bit line contact pad and method for forming the same	438/258	257/E21.59; 257/E21.682;		Lee, Seung-Min et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
12	<input type="checkbox"/>	<input type="checkbox"/>	US 20030215978	20031120	15	Method for making tapered opening for programmable resistance memory	438/95	257/E45.002		Maimon, Jon et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
13	<input type="checkbox"/>	<input type="checkbox"/>	US 20030181052	20030925	16	Method of forming integrated circuit structures in silicone ladder polymer	438/694	257/E21.026; 257/E21.256;		Rasmussen, Robert	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
14	<input type="checkbox"/>	<input type="checkbox"/>	US 20030134473	20030717	10	Novel process for flash memory cell	438/257			Sung, Hung-Cheng et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
15	<input type="checkbox"/>	<input type="checkbox"/>	US 20030124801	20030703	19	Method for fabricating flash memory cell	438/257			Lin, Chi-Hui	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003
16	<input type="checkbox"/>	<input type="checkbox"/>	US 20030100172	20030529	27	Gate-contact structure and method for forming the same	438/585			Kim, Sun-Young et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2003

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Default operator: OR

9 and trench

8/09/04

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7	<input type="checkbox"/>	US 20040036124	20040226	18	Inverted staggered thin film transistor with salicidized source/drain structures	257/382	257/383; 257/384		Vyvoda, Michael A. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004	
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